

Atomistic Simulation Study of the Crystal-Melt Interface Excess Stresses

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Introduction

For the solid-liquid interface system, the EIS plays a role in many aspects. i) The magnitude of τ_{mn} and its crystalline anisotropy provide practical knowledge of γ in predicting solidification microstructure evolution; ii) The divergence of the EIS contributes to the mechanical force balances at crystal-melt interfaces (CMIs); The EIS is an essential factor in the non-equilibrium nucleation process.; The non-uniformly distributed local stress shifts the equilibrium composition or the mutual miscibilities at the interfacial region away from their unstressed bulk values.

For quantifying the work of elastic stretching/compressing a solid surface, e.g., Shuttleworth derived the equation that associating the surface (or solid-vapor interface) free energy γ with the surface (or solid-vapor interface) stress tensor τ_{mn} ,



System: BCC: Fe, Nb, soft-sphere; FCC: Ni. Potential: EAM, MEAM, SS

FIG.2 Schematic illustration of the CMIs built in the current MD simulations. The two CMIs parallel to the xy plane (separated over 20 times of the lattice parameters

Simulation Details

$$\tau_{mn} = \delta_{mn}\gamma + \frac{\sigma_{1}}{\partial e_{mn}}$$

in which, δmn is the Kronecker delta, and e_{mn} is the surface strain tensor. m, n = x, y are the two Cartesian axial directions parallel to the surface. [Phys. Rev. B 79, 054109(2009); Phys. Rev. B 79,045430(2009); J. Chem. Phys. 131,114110(2009)]

Microscopic Pressure Definitions

The first definition method is so-called the virial method.

$$s_{i}^{\alpha\beta} = -\left[mv_{i\alpha}v_{i\beta} + \frac{1}{2}\sum_{j=1}^{N_{n}}\left(r_{i\alpha}f_{i\beta} + r_{j\alpha}f_{j\beta}\right)\right] \quad P_{\alpha\beta}^{\rm VM}(z) = -\frac{\left\langle\sum_{i}^{N_{z}}s_{i}^{\alpha\beta}(z)\right\rangle}{A\Delta z}$$

where α , β take on values x, y, z, m is particle mass, v_i is the velocity of particle i. r_{ii} and f_{ij} are the distance and force between particle *i* and particle *j* connected with a pairwise potential. N_n is the number of particle *i*'s neighboring particles. The VM pressure components profiles along the CMI normal, $P_{\alpha\beta}^{VM}(z)$, are determined in fine-graining z axis (with bin size Δz , see details below), and calculated as the sum of the negative perparticle stress tensors $S_i^{\alpha\beta}$ divided by bin volume and the summation run over Nz particles located between z and $z + \Delta z$, here A is the cross-section area.

The second definition method is the well-known Irving-Kirkwood contour method (hereafter, referred as IK for simplicity).

$$(\Delta z/|z_{ii}|, Z_i + \Delta z/2 < z < Z_i - \Delta z/2)$$

in z) giving a total of forty independent samples (20 replica runs) to determine statistical uncertainty. The simulation box contains crystal, melt, and vapor phases for the metal systems, while for the SS system, the vapor regions are removed due to the crystal and melt phases coexist under the finite value of the hydrostatic pressures.

[Philos. Mag. 83 (35) 3977–3994(2002); Phys. Rev. B 81, 144119(2010); Phys. Rev. B 33 (12) (1986); Comput. Mater. Sci. 161 (2019); Phys. Rev. Lett. 94 (8) (2005), 086102]

Interface Characterization

The fine-grained density profile across the interface, $\rho(z)$, is computed as the average number of atoms in each discrete bin of spacing Δz divided by the volume of the bin, $A\Delta z$, 1 11 \

$$\rho(z) = \frac{\langle N_z \rangle}{A\Delta z}$$

The fine-grained stress profile is defined as the between the fine-grained normal and transverse components of the pressure tensor. τ is calculated by integrating the stress profile over the entire length of the simulation cell.

$$S^{\text{VM,IK}}(z) = P_{zz}^{\text{VM,IK}}(z) - \frac{1}{2} \left[P_{xx}^{\text{VM,IK}}(z) + P_{yy}^{\text{VM,IK}}(z) \right] \qquad \tau^{\text{VM,IK}} = \int_{0}^{L_{z}} S^{\text{VM,IK}}(z) dz$$

$$\xrightarrow{-40 - 20 \ 0 \ 20 \ 40}_{-40 \ -20 \ 0 \ 20 \ 40} \qquad FIG.3 \text{ Significant difference found in the pressure component profiles i.e.}$$



 k_B is the Boltzmann constant, ρ is number density, $\delta_{\alpha\beta}$ is the Dirac delta function, N is the number of particles in the whole system. Z_i

FIG.1 Illustration of a particle pair (*i* and *j*) that contributes to the fine-scale IK pressure, in a flat plane in Cartesian coordinates. The double-heads arrows denote different integration cases. [Mol. Simul. 29, 101–109(2003); Mol. Phys. 48,1357–1368(1983)]





Result and Discussion





z (Å) FIG.4 (a)-(c) snapshots of the equilibrated BCC Fe FIG.5 The coarse-scale transverse Fig. 8. (a)-(d) show representative snapshots Fig. 9. The coarse-scale transverse (100), (110), and (111) CMIs ; (d)-(f) the fine- pressure tensor components(a)(b), grained density profiles for the three BCC CMIs and stress profiles(c)



FIG.6 (a)-(c) snapshots of the equilibrated BCC Fe (100), (110), and (111) CMIs ; (d)-(f) the finegrained density profiles for the three BCC CMIs

FIG.7 The coarse-scale transverse pressure tensor components(a)(b), and stress profiles(c)

from equilibrated BCC (111) CMIs modeled pressure tensor components profiles (a) with four different potentials, under each and stress profiles S(z) (c) across the melting point temperatures. Viewpoints are four BCC (111) CMIs. The two (x and y) same as Fig. 4(a). Panel (e)-(h) show the components for BCC (111) CMI are corresponding fine-grained density profiles. isotropic. The result of MEAM Nb (blue The zero points of z corresponding to the GDS dashed line) are only calculated with are chosen that the excess number of particles VM definition. equals zero.

 $z(\sigma)$

 $z(\sigma)$

-20

-10

z (Å)

20

10

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